MCR8DCM

MCR8DCN

Motorola Preferred Devices

SCRs 8.0 AMPERES RMS

Silicon Controlled Rectifiers Reverse Blocking Thyristors

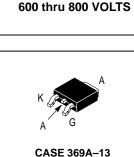
Designed for high volume, low cost, industrial and consumer applications such as motor control; process control; temperature, light and speed control.

- Small Size
- Passivated Die for Reliability and Uniformity
- Low Level Triggering and Holding Characteristics
- Available in Two Package Styles Surface Mount Lead Form — Case 369A Miniature Plastic Package — Straight Leads — Case 369

ORDERING INFORMATION

- To Obtain "DPAK" in Surface Mount Leadform (Case 369A) Shipped in Sleeves — No Suffix, i.e. MCR8DCN Shipped in 16 mm Tape and Reel — Add "T4" Suffix to Device Number, i.e. MCR8DCNT4
- To Obtain "DPAK" in Straight Lead Version (Case 369) Shipped in Sleeves Add "–1" Suffix to Device Number, i.e. MCR8DCN–1

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted)



STYLE 4

Rating		Symbol	Value	Unit
Peak Repetitive Off–State Voltage (1) Peak Repetitive Reverse Voltage (T _J = -40 to 125°C)	MCR8DCM MCR8DCN	VDRM VRRM	600 800	Volts
On–State RMS Current (All Conduction Angles; T _C = 105°C)		^I T(RMS)	8.0	Amps
Average On–State Current (All Conduction Angles; $T_C = 105^{\circ}C$)		I _{T(AV)}	5.1	
Peak Non–Repetitive Surge Current (One Half Cycle, 60 Hz, T _J = 125°C)		ITSM	80	
Circuit Fusing Consideration (t = 8.3 msec)		l ² t	26	A ² sec
Peak Gate Power (Pulse Width \leq 10 μ sec, T _C = 105°C)		PGM	5.0	Watts
Average Gate Power (t = 8.3 msec, T _C = 105°C)		PG(AV)	0.5	
Peak Gate Current (Pulse Width \leq 10 µsec, T _C = 105°C)		I _{GM}	2.0	Amps
Operating Junction Temperature Range		ТJ	-40 to 125	°C
Storage Temperature Range		T _{stg}	-40 to 150	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance — Junction to Case — Junction to Ambient — Junction to Ambient ⁽²⁾	R _θ JC R _θ JA R _θ JA	2.2 88 80	°C/W
Maximum Lead Temperature for Soldering Purposes (3)	тլ	260	°C

(1) V_{DRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the device are exceeded.

(2) Surface mounted on minimum recommended pad size.

(3) 1/8" from case for 10 seconds.

Preferred devices are Motorola recommended choices for future use and best overall value.



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ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

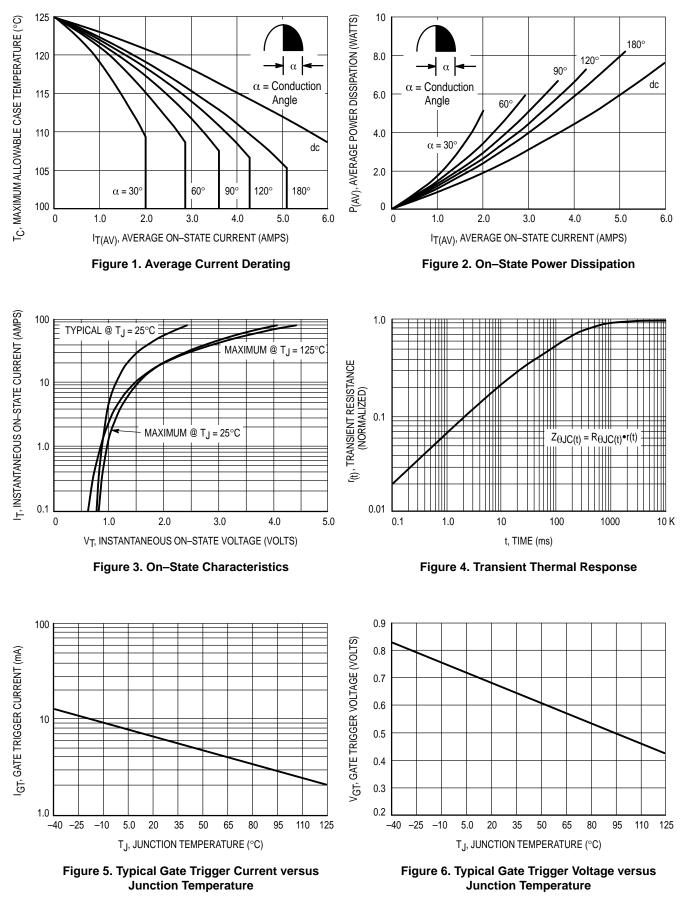
Characteristics	Symbol	Min	Тур	Max	Unit
Peak Forward Blocking CurrentPeak Reverse Blocking Current $(V_{AK} = Rated V_{DRM} \text{ or } V_{RRM}, Gate Open)$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	IDRM IRRM			0.01 5.0	mA
Peak On–State Voltage (1) (I _{TM} = 16 A)	VTM	_	1.4	1.8	Volts
Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = 25^{\circ}\text{C})$ $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = -40^{\circ}\text{C})$	lgt	2.0	7.0 —	15 30	mA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = 25^{\circ}\text{C})$ $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = -40^{\circ}\text{C})$ $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = 125^{\circ}\text{C})$	V _{GT}	0.5 — 0.2	0.65 — —	1.0 2.0 —	Volts
Holding Current ($V_D = 12 V$, $I_T = 200 mA$, $T_J = 25^{\circ}C$) ($V_D = 12 V$, $I_T = 200 mA$, $T_J = -40^{\circ}C$)	ΙΗ	4.0	22 —	30 60	mA
Latching Current ($V_D = 12 V$, $I_G = 15 mA$, $T_J = 25^{\circ}C$) ($V_D = 12 V$, $I_G = 30 mA$, $T_J = -40^{\circ}C$)	ιL	4.0	22 —	30 60	mA

DYNAMIC CHARACTERISTICS

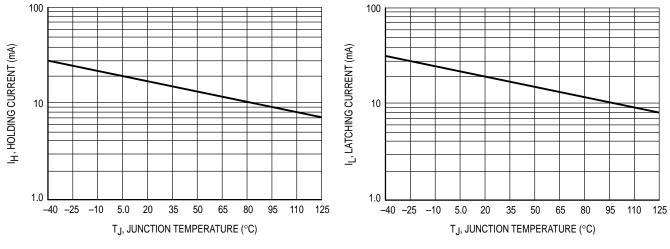
Characteristics	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Off-State Voltage	dv/dt				V/μs
(V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T_J = 125°C)		50	200	—	

(1) Pulse Test; Pulse Width \leq 2.0 msec, Duty Cycle \leq 2%.

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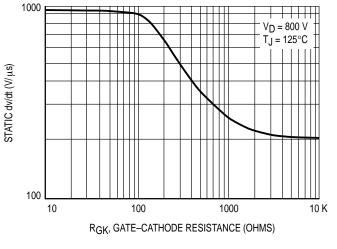
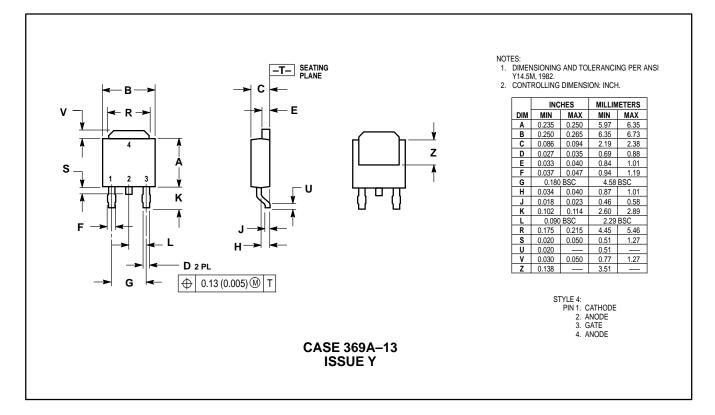


Figure 9. Exponential Static dv/dt versus Gate–Cathode Resistance

PACKAGE DIMENSIONS



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